Amendments to the Claims:

Following is a listing of all claims in the present application, which listing supersedes all previously presented claims:

Listing of Claims:

1. (Original) An electron beam lithography apparatus for providing a one-to-one projection of a pattern, comprising:

a pyroelectric emitter, which is disposed a predetermined distance apart from a substrate holder, the pyroelectric emitter including a pyroelectric plate having a dielectric plate on a surface thereof and a patterned semiconductor thin film on the dielectric plate facing the substrate holder;

a heating source for heating the pyroelectric emitter; and

a pair of magnets disposed beyond the pyroelectric emitter and the substrate holder, respectively, to control paths of electrons emitted by the pyroelectric emitter.

2. (Original) The apparatus as claimed in claim 1, wherein each of the pair of magnets is an electromagnet or a permanent magnet.

3. (Original) The apparatus as claimed in claim 1, further comprising an adhesion layer having a predetermined thickness between the pyroelectric plate and the dielectric plate.

4. (Original) The apparatus as claimed in claim 1, wherein the heating source is a contact-type heating plate using resistive-type heating.

5. (Original) The apparatus as claimed in claim 1, wherein the heating source is a remotely controlled heater that generates infrared rays.

6. (Original) The apparatus as claimed in claim 1, wherein the pyroelectric plate is formed of a pyroelectric material selected from the group consisting of $LiNbO_3$, $LiTaO_3$, $BaTiO_3$, and $Pb(Zr,Ti)O_3$.

7. (Original) The apparatus as claimed in claim 1, wherein the dielectric plate is a sapphire plate.

8. (Original) The apparatus as claimed in claim 1, wherein the dielectric plate has a thickness in a range of about 0.1 to about 1 mm.

9. (Original) The apparatus as claimed in claim 1, wherein the semiconductor thin film is a silicon thin film.

10. (Original) The apparatus of claim 1, wherein the semiconductor thin film has a thickness in a range of about 100 to about 10,000 Å.

11. (Original) An electron beam lithography apparatus for providing an x-to-one projection of a pattern, comprising:

a pyroelectric emitter, which is disposed a predetermined distance apart from a substrate holder, the pyroelectric emitter including a pyroelectric plate having a dielectric plate on a surface thereof and a patterned semiconductor thin film on the dielectric plate facing the substrate holder;

a heating source for heating the pyroelectric emitter; and

a deflection unit disposed between the pyroelectric emitter and the substrate holder to control paths of electrons emitted by the pyroelectric emitter.

12. (Original) The apparatus as claimed in claim 11, further comprising an adhesion layer having a predetermined thickness between the pyroelectric plate and the dielectric plate.

13. (Original) The apparatus as claimed in claim 11, wherein the deflection unit comprises:

deflection plates for deflecting electrons emitted from the pyroelectric emitter; and

at least one magnetic lens for focusing the deflected electrons.

14. (Original) The apparatus as claimed in claim 11, wherein the heating source is a contact-type heating plate using resistive-type heating.

15. (Original) The apparatus as claimed in claim 11, wherein the heating source is a remotely controlled heater that generates infrared rays.

16. (Original) The apparatus as claimed in claim 11, wherein the pyroelectric plate is formed of a pyroelectric material selected from the group consisting of $LiNbO_3$, $LiTaO_3$, $BaTiO_3$, and $Pb(Zr,Ti)O_3$.

17. (Original) The apparatus as claimed in claim 11, wherein the dielectric plate is a sapphire plate.

18. (Original) The apparatus as claimed in claim 11, wherein the dielectric plate has a thickness in a range of about 0.1 to about 1 mm.

19. (Original) The apparatus as claimed in claim 11, wherein the semiconductor thin film is a silicon thin film.

20. (Original) The apparatus as claimed in claim 11, wherein the semiconductor thin film has a thickness in a range of about 100 to about 10,000 Å.

21. (Currently Amended) A method of fabricating a pyroelectric emitter, ~~which is disposed a predetermined distance apart from a substrate holder, the pyroelectric emitter including a pyroelectric plate having a dielectric plate on a surface thereof and a patterned semiconductor thin film on the dielectric plate facing the substrate holder, the method~~ comprising:

preparing a pyroelectric plate;

preparing a patterned mask of a semiconductor material, the semiconductor material being sufficiently thick in desired portions to prevent electrons emitted by the pyroelectric plate during heating from being further transmitted ~~by forming a patterned semiconductor thin film on a dielectric plate having a predetermined thickness~~; and

disposing the patterned mask [[on]] adjacent the surface of the pyroelectric plate.

22. (Currently Amended) The method as claimed in claim 21, wherein preparing the patterned mask comprises:

sequentially forming a semiconductor thin film having a predetermined thickness and a resist on [[the]] a dielectric plate having the predetermined thickness;

patterning the resist in a predetermined pattern;

patterning the semiconductor thin film using the patterned resist as a mask; and

removing the patterned resist.

23. (Currently Amended) The method as claimed in claim 21, wherein disposing the patterned mask [[on]] adjacent the pyroelectric plate comprises forming an adhesion layer on the pyroelectric plate and adhering the patterned mask on the adhesion layer.

24. (Original) The method as claimed in claim 21, wherein the pyroelectric plate is formed of a pyroelectric material selected from the group consisting of $LiNbO_3$, $LiTaO_3$, $BaTiO_3$, and $Pb(Zr,Ti)O_3$.

25. (Currently Amended) The method as claimed in claim 21, wherein the patterned mask is on a dielectric plate ~~is formed of sapphire~~.

26. (Currently Amended) The method as claimed in claim [[21]] 25, wherein the dielectric plate is formed to a thickness in a range of about 0.1 to about 1 mm.

27. (Currently Amended) The method as claimed in claim 21, wherein the semiconductor material is ~~thin film is formed of~~ silicon.

28. (Currently Amended) The method as claimed in claim 21, wherein the semiconductor material ~~thin film~~ is formed to a thickness in a range of about 100 to about 10,000 Å.